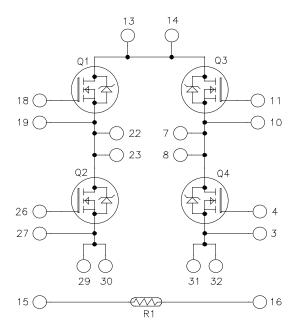
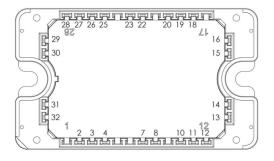
MSCSM120HM16T3AG

Full Bridge SiC MOSFET Power Module

Product Overview

The MSCSM120HM16T3AG device is a full bridge 1200V, 173A silicon carbide (SiC) power module.





Notes:

- All ratings at T_J = 25 °C, unless otherwise specified.
- All multiple inputs and outputs must be shorted together. For example, 13/14; 29/30; 22/23, and so on.

⚠ CAUTION

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of the MSCSM120HM16T3AG device:

- · SiC Power MOSFET
 - Low R_{DS(on)}
 - High temperature performance
- · Very low stray inductance
- Internal thermistor for temperature monitoring
- · Aluminum Nitride (AIN) substrate for improved thermal performance

Benefits

The following are the benefits of the MSCSM120HM16T3AG device:

- · High power and efficiency converters and inverters
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- · Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- · Low profile
- **RoHS Compliant**

Applications

The following are the applications of the MSCSM120HM16T3AG device:

- · Uninterruptible power supplies
- · Welding converters
- · Switched mode power supplies
- · EV motor and traction drive

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1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120HM16T3AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings of the MSCSM120HM16T3AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit	
V _{DSS}	Drain-Source voltage	rain-Source voltage		V	
I _D	<u> </u>		173 ¹	Α	
			138 ¹		
I _{DM}	Pulsed drain current	ulsed drain current			
V _{GS}	Gate-Source voltage	Gate-Source voltage		V	
R _{DS(on)}	Drain-Source ON resistance		16	mΩ	
P _D	Power dissipation	T _C = 25 °C	745	W	

Note:

1. Specification of SiC MOSFET device but output current must be limited due to size of power connectors.

The following table lists the electrical characteristics of the MSCSM120HM16T3AG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V V _{DS} = 1200V		_	20	200	μΑ
R _{DS(on)}	Drain-Source on	V _{GS} = 20V	T _J = 25 °C	_	12.5	16	mΩ
resistance		I _D = 80A	T _J = 175 °C	_	20	_	
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 6 \text{ mA}$		1.8	2.8	_	V
I _{GSS}	Gate-Source leakage current	V _{GS} = 20V V _{DS} = 0V		_	_	200	nA

The following table lists the dynamic characteristics of the MSCSM120HM16T3AG device.

Table 1-3. Dynamic Characteristics

Symb ol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V		_	6040	_	pF
C _{oss}	Output capacitance	V _{DS} = 1000V f = 1 MHz		_	540	_	
C _{rss}	Reverse transfer capacitance			_	50	_	
Q_g	Total gate charge	$V_{GS} = -5V/20V$		_	464	_	nC
Q_{gs}	Gate-source charge	V _{Bus} = 800V I _D = 80A		_	82	_	
Q_{gd}	Gate-drain charge			_	100	_	
T _{d(on)}	Turn-on delay time	$V_{GS} = -5V/20V$		_	30	_	ns
T _r	Rise time	V _{Bus} = 600V		_	30	_	
T _{d(off)}	Turn-off delay time	I _D = 100A		_	50	_	
T _f	Fall time	$R_{GON} = 4\Omega$ $R_{GOFF} = 2.4\Omega$			25	_	
E _{on}	Turn-on energy	V _{GS} = -5V/20V	T _J = 150 °C	_	2.4	_	mJ
E _{off}	Turn-off energy	V_{Bus} = 600V I_{D} = 100A R_{GON} = 4 Ω R_{GOFF} = 2.4 Ω		_	1.3	_	mJ
R _{Gint}	Internal gate resistance			_	2.94	_	Ω
R _{thJC}	Junction-to-case the	ermal resistance		_	_	0.2	°C/W

The following table lists the body diode ratings and characteristics of the MSCSM120HM16T3AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode forward voltage	V _{GS} = 0V	_	4	_	V
		I _{SD} = 80A				
		V _{GS} = -5V	_	4.2	_	
		I _{SD} = 80A				
t _{rr}	Reverse recovery time	I _{SD} = 80A	_	90	_	ns
Q _{rr}	Reverse recovery charge	$V_{GS} = -5V$	_	1100	_	nC
I _{rr}	Reverse recovery current	V _R = 800V		27	_	Α
		$di_F/dt = 2000 A/\mu s$				

1.2 Thermal and Package Characteristics

The following table lists the package characteristics of the MSCSM120HM16T3AG device.

Table 1-5. Thermal and Package Characteristics

Symbol	Characteristic			Min.	Max.	Unit
V _{ISOL}	RMS isolation voltage, any terminal to ca	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz			_	V
T _J	Operating junction temperature range	Operating junction temperature range			175	°C
T _{JOP}	Recommended junction temperature und	Recommended junction temperature under switching conditions			T _{Jmax} –25	
T _{STG}	Storage temperature range	Storage temperature range				
T _C	Operating case temperature	Operating case temperature			125	
Torque	Mounting torque	2	3	N.m		
Wt	Package weight			_	110	g

The following table lists the temperature sensor NTC of the MSCSM120HM16T3AG device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristic		Min.	Тур.	Max.	Unit
R ₂₅	Resistance at 25°C		_	50	_	kΩ
$\Delta R_{25}/R_{25}$	_	_	_	5	_	%
B _{25/85}	T ₂₅ = 298.15 K	_	_	3952	_	K
ΔΒ/Β	_	T _C = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature R_T: Thermistor value at T

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

1.3 Typical SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the MSCSM120HM16T3AG device.

Figure 1-1. Maximum Thermal Impedance

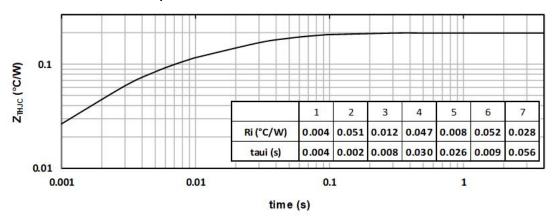


Figure 1-2. Output Characteristics, $T_J = 25$ °C

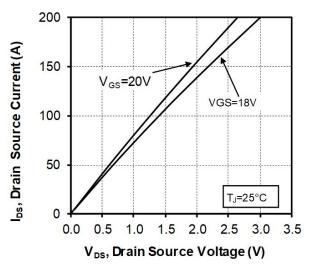


Figure 1-3. Output Characteristics, T_J = 175 °C

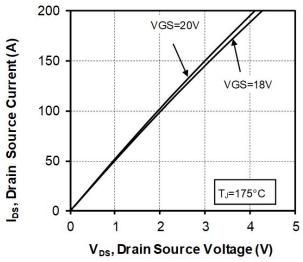


Figure 1-4. Normalized R_{DS(on)} vs. Temperature

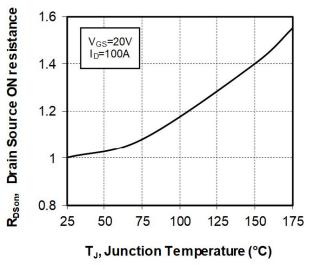


Figure 1-5. Transfer Characteristics

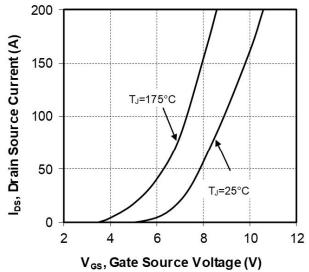


Figure 1-6. Switching Energy vs. Rg

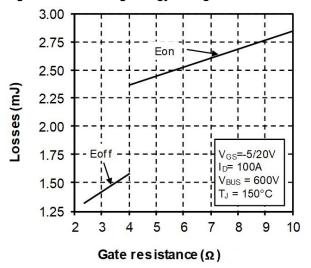


Figure 1-7. Switching Energy vs. Current

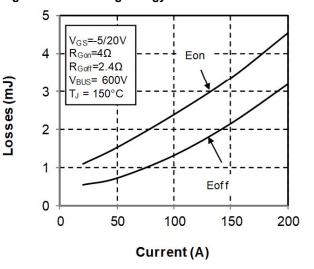


Figure 1-8. Capacitance vs. Drain Source Voltage

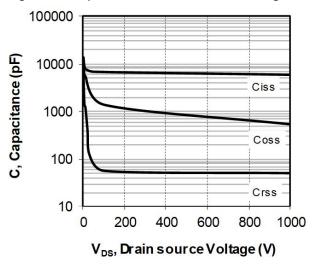


Figure 1-9. Gate Charge vs. Gate Source Voltage

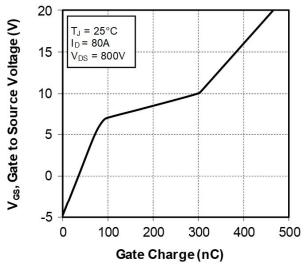


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

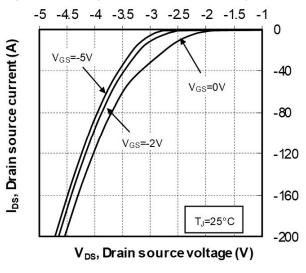


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

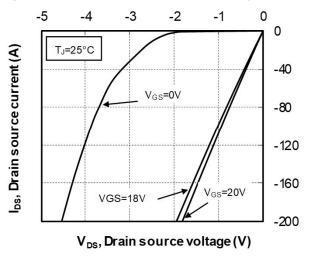
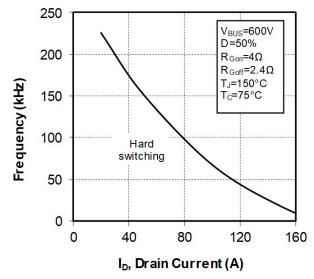


Figure 1-12. Body Diode Characteristics, T_J = 175 °C Figure 1-13. 3rd Quadrant Characteristics, T_J = 175 °C -4.5 -4 -3.5 -3 -2.5 -2 -1.5 -1 -5 -2 0 0 los, Drain source current (A) l_{DS}, Drain source current (A) T_J=175°C V_{GS}=-5V -40 -40 V_{GS}=-2V -80 -80 V_{GS}=0V VGS=18V V_{GS}=0V -120 -120 -160 -160 T_J=175°C V_{GS}=20V -200 -200 V_{DS}, **D**rain source voltage (V) V_{DS}, Drain source voltage (V)

Figure 1-14. Operating Frequency vs. Drain Current



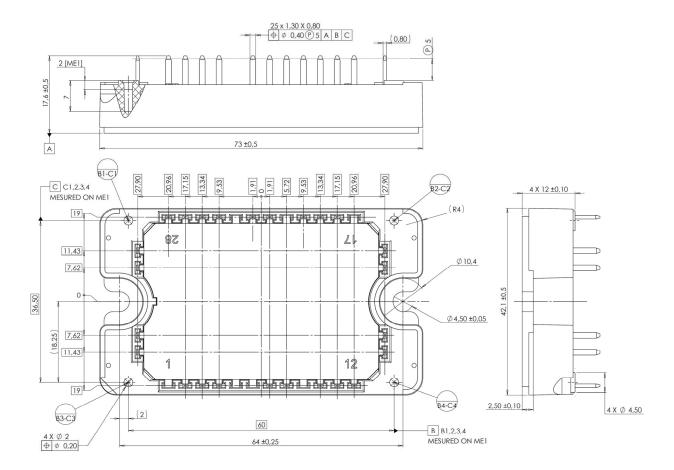
2. Package Specifications

The following section shows the package specification of the MSCSM120HM16T3AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120HM16T3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See AN3500A—Mounting Instructions for SP1F and SP3F Power Modules for more Information.

MSCSM120HM16T3AG

Revision History

3. Revision History

Revision	Date	Description
Α	06/2022	Initial Revision

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